Square aluminium MOS-capacitors ($250 \times 250\mu\text{m}^2$ and $500 \times 500\mu\text{m}^2$) were fabricated on $R_S = 48.3\Omega$ Si wafers and tested. Following SC-1/SC-2 of the bare wafers, a 454 ± 5nm-thick oxide was grown by 1-hour dry oxidation at 1000°C. About $2500\mathring{A}$ of aluminum was deposited[1] via PVD, and the backside oxide was etched. The metal was patterned via 365nm lithography, and the final product was sintered for 15 minutes at 425°C.

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[1] Measured values haven't been posted on Stellar by time of writing